

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	0	"20010048114".pn. and switch	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/03 13:55
L2	0	"5146465".pn. and switch	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/03 13:56
L3	0	"6661822".pn. and switch	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/03 13:56
L4	33	(nitride adj semiconductor) and (optical adj switch)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/03 14:12
L5	372	amano-hiroshi.inv.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/03 14:12
S1	2	"5146465".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/29 10:06
S2	2	"6259122".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/29 10:06
S3	2	"5875052".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/29 10:07

S4	2	"6306672".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/29 10:07
S5	2	"6046464".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/29 10:07
S6	2	"6440823".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/29 10:08
S7	2	"5929467".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/29 10:08
S8	2	"5923058".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/29 10:09
S9	2	"5228044".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/29 10:09
S10	2	"5235194".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/29 10:09
S11	2	"5273933".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/29 10:10

S12	2	"5317167".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/29 10:10
S13	2	"5432808".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/29 10:10
S14	2	"5617438".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/29 10:10
S15	3	"5740192".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/29 10:11
S16	3	"5998810".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/29 10:11
S17	2	"6242764".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/29 10:11
S18	2	"5990495".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/29 10:12
S19	3	"5656832".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/29 10:12

S20	3	"5909040".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/29 10:13
S21	3	"5929466".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/29 10:14
S22	2	"4792958".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/29 10:14
S23	2	"4809287".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/29 10:15
S24	5	"435117".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/29 10:15
S25	2	"4835117".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/29 10:15
S26	2	"4949349".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/29 10:16
S27	2	"4910743".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/29 10:16

S28	2	"4928285".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/29 10:16
S29	2	"4893313".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/29 10:16
S30	2	"5076800".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/29 10:19
S31	2	"5036521".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/29 10:19
S32	2	"5168077".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/29 10:19
S33	2	"5042043".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/29 10:20
S34	2	"5005057".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/29 10:20
S35	2	"5079184".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/29 10:20

S36	2	"5103271".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/29 12:07
S37	2	"5146465".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/29 12:31
S38	1	"5146465".pn. and thickness	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/29 13:53
S39	1594	("al.sub.xga.sub.1-xn" or algan or (aluminum adj gallium adj nitride)) and (aln or (aluminum adj nitride)) and sapphire and thickness	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/29 13:59
S40	1612	("Al.sub.x Ga.sub.1-x N" or algan or (aluminum adj gallium adj nitride)) and (aln or (aluminum adj nitride)) and sapphire and thickness	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/29 14:00
S41	8	("Al.sub.x Ga.sub.1-x N" or algan or (aluminum adj gallium adj nitride)) and (aln or (aluminum adj nitride)) and sapphire and thickness and (carbon near concentration)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/29 14:09
S42	5	(carbon near concentration near (aln or (aluminum adj nitride)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/29 14:41
S43	27	(carbon with concentration with (aln or (aluminum adj nitride)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/29 14:17

S44	1	(carbon near (doped or dopant) near (aln or (aluminum adj nitride)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/29 14:17
S45	1	(carbon near (doped or dopant) near (AlN or (aluminum adj nitride)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/29 14:18
S46	44	(carbon with (doped or dopant) with (AlN or (aluminum adj nitride)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/30 11:48
S47	121	(carbon with (diffused or impurity or implant) with (AlN or (aluminum adj nitride)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/29 14:28
S48	1	(c near concentration near (aln or (aluminum adj nitride)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/29 14:46
S49	0	(aln or (aluminum adj nitride)) near thickness near protection	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/29 14:47
S50	7	(aln or (aluminum adj nitride)) near thickness near protective	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/29 14:50
S51	0	(aln or (aluminum adj nitride)) near thickness near prevent	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/29 14:50

S52	0	(aln or (aluminum adj nitride)) near thickness near preventive	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/29 14:50
S53	0	(aln or (aluminum adj nitride)) near thickness near prevention	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/29 14:50
S54	0	(aln or (aluminum adj nitride)) near thickness near stop	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/29 14:50
S55	0	(aln or (aluminum adj nitride)) near thickness near halt	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/29 14:51
S56	0	(aln or (aluminum adj nitride)) near thickness near ((ga or gallium) near evaporating)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/29 14:52
S57	0	(aln or (aluminum adj nitride)) near thickness near ((ga or gallium) near evaporated)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/29 14:52
S58	0	(aln or (aluminum adj nitride)) near thickness near ((ga or gallium) near evaporate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/29 14:52
S59	0	(aln or (aluminum adj nitride)) near thickness near ((ga or gallium) near evaporation)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/29 14:52

S60	407	(aln or (aluminum adj nitride)) adj thickness	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/29 14:53
S61	43	((aln or (aluminum adj nitride)) adj thickness) and (nitride adj semiconductor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/29 15:29
S62	0	(aln or (aluminum adj nitride)) near ("Al.sub.x Ga.sub.1-x N" or AlGaN or (aluminum adj gallium adj nitride)) near evaporation	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/29 15:32
S63	8	(aln or (aluminum adj nitride)) with ("Al.sub.x Ga.sub.1-x N" or AlGaN or (aluminum adj gallium adj nitride)) with evaporation	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/29 15:37
S64	7	(aln or (aluminum adj nitride)) adj protection adj layer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/29 17:13
S65	44	(aln or (aluminum adj nitride)) adj protective adj layer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/29 17:13
S66	21	(aln or (aluminum adj nitride)) adj protective adj film	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/29 17:14
S67	2	(aln or (aluminum adj nitride)) adj protection adj film	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/29 16:32

S68	1	(aln or (aluminum adj nitride)) near ("Al.sub.x Ga.sub.1-x N" or AlGaN or (aluminum adj gallium adj nitride)) near alternating	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/29 16:48
S69	21	(aln or (aluminum adj nitride)) with ("Al.sub.x Ga.sub.1-x N" or AlGaN or (aluminum adj gallium adj nitride)) with alternating	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/29 17:15
S70	3	(aln or (aluminum adj nitride)) with ("Al.sub.x Ga.sub.1-x N" or AlGaN or (aluminum adj gallium adj nitride)) with alternate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/29 17:07
S71	168	kubota-shinichi.inv.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/29 17:25
S72	25	horino-kazuhiko.inv.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/29 17:08
S73	61	kuramata-akito.inv.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/29 17:09
S74	0	(aln or (aluminum adj nitride)) adj protection adj layer near thickness	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/29 17:13
S75	4	(aln or (aluminum adj nitride)) adj protective adj layer near thickness	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/29 17:14

S76	3	(aln or (aluminum adj nitride)) adj protective adj film near thickness	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/29 17:14
S77	2	(aln or (aluminum adj nitride)) with ("Al.sub.x Ga.sub.1-x N" or AlGaN or (aluminum adj gallium adj nitride)) with alternating with thickness	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/29 17:15
S78	41	ohba-yasuo.inv.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/29 17:35
S79	2	"6661822".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/29 17:36
S80	2	"6661822".pn. and thickness	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/29 17:41
S81	1	"6661822".pn. and single	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/29 18:42
S82	2	"6661822".pn. and protect\$	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/29 19:48
S83	0	"6661822".pn. and monocrystal\$	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/29 18:43

S84	1	"6661822".pn. and crystal\$	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/29 19:23
S85	1	"5146465".pn. and thickness	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/29 19:23
S86	2	"6661822".pn. and active	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/29 20:30
S87	34	(active adj layer) near (GaInN or "Ga. sub.x In.sub.1-x N")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/29 20:57
S88	1	"20040213309".pn. and injection	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/29 20:30
S89	34	(active adj layer) near (GaInN or "Ga. sub.x In.sub.1-x N" or "ga.sub.xin.sub. 1-xn")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/29 20:58
S90	33	(active adj layer) near (GaInN or "Ga. sub.z In.sub.1-z N" or "ga.sub.xin.sub. 1-xn")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/29 21:00
S91	177	(active adj layer) with (GaInN or "Ga. sub.z In.sub.1-z N" or "ga.sub.xin.sub. 1-xn")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/29 21:14

S92	175	(active adj layer) with (GaInN or "Ga.sub.1-z In.sub.z N" or "ga.sub.1-xin.sub.xn")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/29 21:15
S93	4	(active adj layer) with ("Ga.sub.1-z In.sub.z N" or "ga.sub.1-xin.sub.xn")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/29 21:24
S94	4	(active adj layer) same ("Ga.sub.1-z In.sub.z N" or "ga.sub.1-xin.sub.xn")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/29 21:25
S95	2	(active adj layer) same ("Ga.sub.1-z In.sub.z N" or "ga.sub.1-zin.sub.zn")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/29 21:25
S96	7	(active adj layer) same ("Ga.sub.1-z In.sub.z N" or "ga.sub.1-yin.sub.yn")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/29 21:36
S97	1	(active adj layer) same ("Ga.sub.1-z In.sub.z N" or "ga.sub.1-yin.sub.yn") and cleavable	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/29 21:37
S98	0	(active adj layer) same ("Ga.sub.1-z In.sub.z N" or "ga.sub.1-yin.sub.yn") and cleav	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/29 21:37
S99	2	(active adj layer) same ("Ga.sub.1-z In.sub.z N" or "ga.sub.1-yin.sub.yn") and cleave	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/29 21:53

S10 0	0	(AlN or (aluminum adj nitride)) near "Al.sub.x Ga.sub.1-x N" near "Al.sub.yGa.sub.yN"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/29 21:54
S10 1	0	(AlN or (aluminum adj nitride)) with "Al.sub.x Ga.sub.1-x N" with "Al.sub.yGa.sub.yN"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/29 21:55
S10 2	0	(AlN or (aluminum adj nitride)) with "Al.sub.x Ga.sub.1-x N" with "Al.sub.yGa.sub.1-yN"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/29 21:55
S10 3	0	(AlN or (aluminum adj nitride)) same "Al.sub.x Ga.sub.1-x N" same "Al.sub.yGa.sub.1-yN"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/29 21:56
S10 4	119	(AlN or (aluminum adj nitride)) same Al _x Ga _{1-x} N same Al _y Ga _{1-y} N	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/29 21:57
S10 5	95	(AlN or (aluminum adj nitride)) same Al _x Ga _{1-x} N same Al _y Ga _{1-y} N same (sapphire adj substrate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/29 21:58
S10 6	0	(AlN or (aluminum adj nitride)) same Al _x Ga _{1-x} N same Al _y Ga _{1-y} N same (sapphire adj substrate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/29 21:58
S10 7	3	(AlN or (aluminum adj nitride)) same Al _x Ga _{1-x} N same Al _y Ga _{1-y} N	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/29 22:01

S10 8	229	(AlN or (aluminum adj nitride)) same AlGaIn same (sapphire adj substrate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/29 22:01
S10 9	78	(AlN or (aluminum adj nitride)) with AlGaIn with (sapphire adj substrate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/30 09:14
S11 0	0	(AlN or (aluminum adj nitride)) near AlGaIn near (sapphire adj substrate).	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/29 22:02
S11 1	2	(lattice adj modification adj (layer or film))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/30 10:18
S11 2	0	"5146465".pn. and (transistor or switch)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/30 10:19
S11 3	0	"5146465".pn. and (fet or switch)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/30 10:45
S11 4	0	"6661822".pn. and (fet or switch)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/30 10:19
S11 5	0	"6661822".pn. and (transistor or switch)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/30 10:28

S11 6	1	"6661822".pn. and (aln and gan)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/30 10:32
S11 7	1	"5146465".pn. and (aln and gan)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/30 12:03
S11 8	8	aln adj gan adj (heterostructure or heterojunction)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/30 10:41
S11 9	1	(aluminum adj nitride) adj (gallium adj nitride) adj (heterostructure or heterojunction)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/30 10:42
S12 0	3	(aluminum adj nitride) near (gallium adj nitride) near (heterostructure or heterojunction)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/30 10:42
S12 1	1	"5915164".pn. and (fet or switch)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/30 10:45
S12 2	253	257/12.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/30 11:48
S12 3	707	257/14.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/30 11:49

S12 4	319	257/15.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/30 11:49
S12 5	333	257/20.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/30 11:49
S12 6	327	257/24.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/30 11:50
S12 7	160	257/11.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/30 11:51
S12 8	330	257/51.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/30 11:52
S12 9	1488	257/66.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/30 11:52
S13 0	372	257/67.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/30 11:53
S13 1	293	257/69.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/30 11:53

S13 2	133	257/70.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/30 11:53
S13 3	202	257/75.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/30 11:54
S13 4	1036	257/94.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/30 11:54
S13 5	610	257/96.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/30 11:55
S13 6	431	257/97.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/30 11:56
S13 7	405	257/101.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/30 11:56
S13 8	555	257/102.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/30 11:56
S13 9	1796	257/103.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/30 11:58

S14 0	743	257/184.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/30 11:58
S14 1	266	257/189.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/30 12:00
S14 2	356	257/615.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/30 12:00
S14 3	2	"5146465".pn. and (laser)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/30 12:04